

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IXTA12N65X2

• FEATURES

- Drain Source Voltage-
 - : V_{DSS}= 650V(Min)
- Static drain-source on-resistance: RDs(on) ≤ 300mΩ@V_{GS}=10V
- Fully characterized avalanche voltage and current
- 100% Avalanche Tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATION

- · Switched mode power supplies
- DC-DC converters

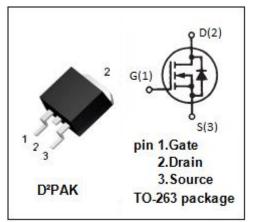
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

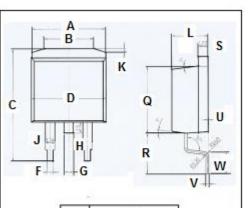
| SYMBOL | PARAMETER | VALUE | UNIT | |
|------------------|---|---------|------|--|
| V _{DSS} | Drain-Source Voltage | 650 | V | |
| V _{GS} | Gate-Source Voltage | ±30 | V | |
| ID | Drain Current-Continuous 12 | | А | |
| I _{DM} | Drain Current-Single Pulsed | 24 | А | |
| P _D | Total Dissipation @T _c =25°C | 180 | W | |
| Tj | Operating Junction Temperature | -55~150 | °C | |
| T _{stg} | Storage Temperature | -55~150 | °C | |

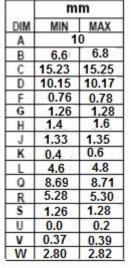
THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | МАХ | UNIT |
|----------------------|-------------------------------------|------|------|
| R _{th(j-c)} | Junction-to-case thermal resistance | 0.69 | °C/W |

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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | МАХ | UNIT |
|---------------------|--------------------------------|--|-----|------|--------------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0V; ID = 250 μ A | 650 | | V |
| $V_{GS(th)}$ | Gate Threshold Voltage | V _{DS} = V _{GS} ; ID = 250 μ A | 2.5 | 4.5 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} =10V; I _D = 6A | | 300 | mΩ |
| I _{GSS} | Gate-Source Leakage Current | V_{GS} = ±30V; V_{DS} =0V | | ±100 | nA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} = V _{DSS} ; V _{GS} = 0V | | 5 | - μ Α |
| | | V _{DS} = V _{DSS} ; V _{GS} = 0V;T _J = 125°C | | 50 | |
| Vsd | Diode forward voltage | I _F = 12A; V _{GS} = 0V | | 1.4 | V |

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